

## SIDC09D60E6

## Fast switching diode chip in EMCON-Technology

### **FEATURES:**

- 600V EMCON technology 70 µm chip
- soft , fast switching
- low reverse recovery charge
- small temperature coefficient

## This chip is used for:

EUPEC power modules and discrete devices



## Applications:

SMPS, resonant applications, drives

Chip Type	$V_R$	I <sub>F</sub>	Die Size	Package	Ordering Code
SIDC09D60E6	600V	20A	3 x 3 mm <sup>2</sup>	sawn on foil	Q67050-A4006- A001

## **MECHANICAL PARAMETER:**

MECHANICAL FARAMETER.		1			
Raster size	3 x 3				
Area total / active	9 / 6.7	mm <sup>2</sup>			
Anode pad size	2.51 x 2.51				
Thickness	70	μm			
Wafer size	150	mm			
Flat position	180	deg			
Max. possible chips per wafer	1667 pcs				
Passivation frontside	Photoimide				
Anode metallisation	3200 nm AlSiCu				
Cathode metallisation	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding				
Die bond	electrically conductive glue or solder				
Wire bond	AI, ≤500μm				
Reject Ink Dot Size	Ø 0.65mm ; max 1.2mm				
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C				



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## **Maximum Ratings**

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$		600	V
Continuous forward current limited by $T_{jmax}$	I <sub>F</sub>		20	
Single pulse forward current (depending on wire bond configuration)	I <sub>FSM</sub>	$t_P = 10 \text{ ms sinusoidal}$ $T_j = 25^{\circ}\text{C}$	80	А
Maximum repetitive forward current limited by T <sub>jmax</sub>	I <sub>FRM</sub>		60	
Operating junction and storage temperature	$T_{\rm j}$ , $T_{ m stg}$		-55+150	°C

## Static Electrical Characteristics (tested on chip), $T_j$ =25 °C, unless otherwise specified

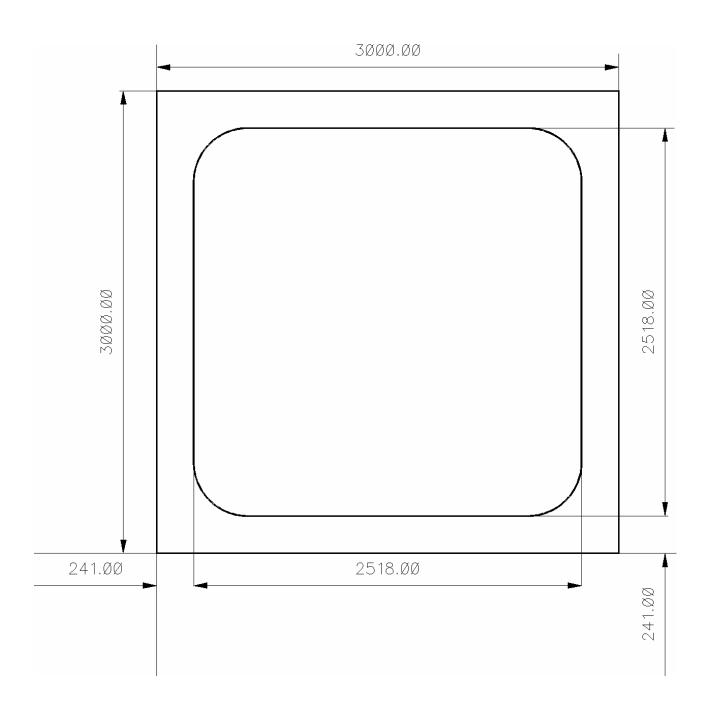
Parameter	Symbol	Condi	Value			Unit	
raiailletei	Syllibol	Conditions		min.	Тур.	max.	
Reverse leakage current	$I_{R}$	V <sub>R</sub> =600V	<i>T<sub>j</sub></i> =25 °C			27	μΑ
Cathode-Anode breakdown Voltage	V <sub>Br</sub>	$I_R=3mA$	<i>T<sub>j</sub></i> =25°C	600			V
Forward voltage drop	$V_F$	I <sub>F</sub> =20A	<i>T<sub>j</sub></i> =25 °C	-	1.25	1.7	V

## **Dynamic Electrical Characteristics,** at $T_j = 25$ °C, unless otherwise specified, tested at component

Parameter	Symbol	Conditions		Value			Unit
raiailletei	Syllibol			min.	Тур.	max.	
Reverse recovery time	t <sub>rr1</sub>	I <sub>F</sub> =20A di/dt=700A/ <b>m</b> s	$T_j = 25$ °C		150		ns
	t <sub>rr2</sub>	$V_R=400V$	$T_j = 125$ °C		200		
Peak recovery current	$I_{RRM1}$	I <sub>F</sub> =20A	$T_j = 25$ °C		20		Α
	$I_{RRM2}$	$di/dt=900A/ms$ $V_R=300V$	$T_j = 125$ °C		25		]^
Reverse recovery charge	Q <sub>rr1</sub>	I <sub>F</sub> =20A	<i>T<sub>j</sub></i> =25 °C		1.7		μC
	Q <sub>rr2</sub>	$di/dt=900A/ms$ $V_R=300V$	T <sub>j</sub> =125°C		2.7		μΟ



## **CHIP DRAWING:**





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#### **FURTHER ELECTRICAL CHARACTERISTICS:**

This chip data sheet refers to the	INFINEON TECHNOLOGIES /	tbd
device data sheet	EUPEC	tbd

#### **Description:**

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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